

DMC201A0

Silicon NPN epitaxial planar type

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C3

■ Basic Part Number

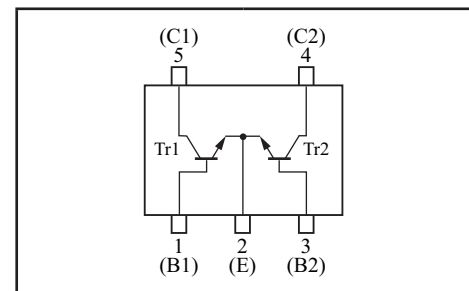
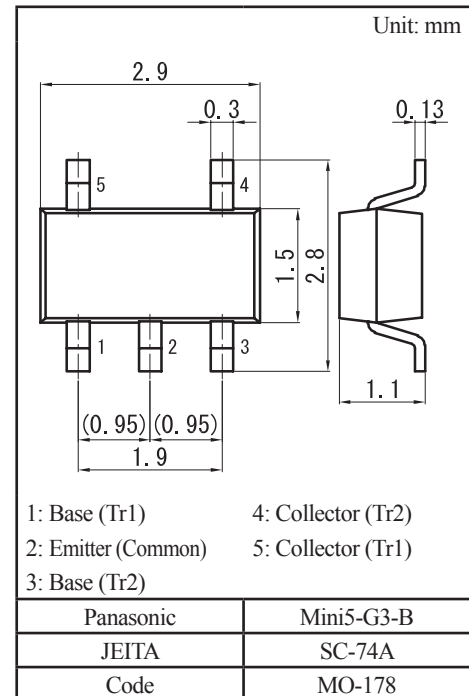
Dual DSC2501 (Common emitter)

■ Packaging

DMC201A00R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1 Tr2	Collector-base voltage (Emitter open)	V_{CBO}	25	V
	Collector-emitter voltage (Base open)	V_{CEO}	20	V
	Emitter-base voltage (Collector open)	V_{EBO}	12	V
	Collector current	I_C	0.5	A
	Peak collector current	I_{CP}	1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	$^\circ\text{C}$
	Operating ambient temperature	T_{opr}	-40 to +85	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



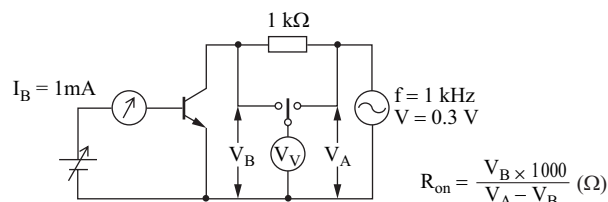
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

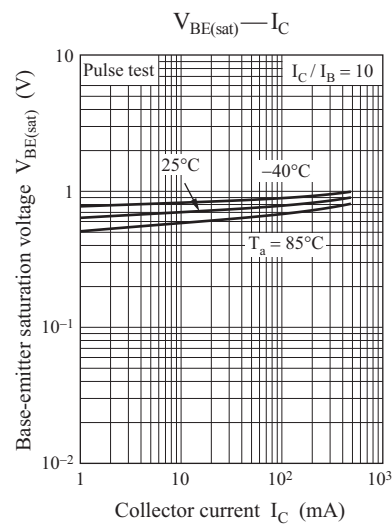
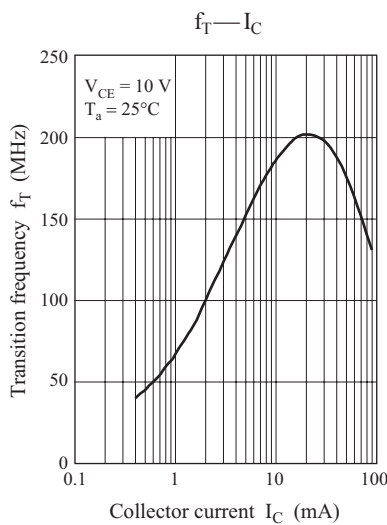
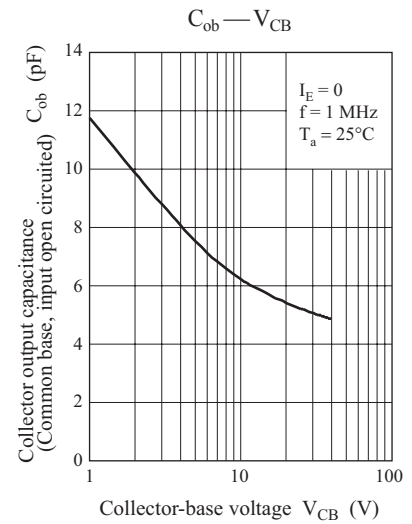
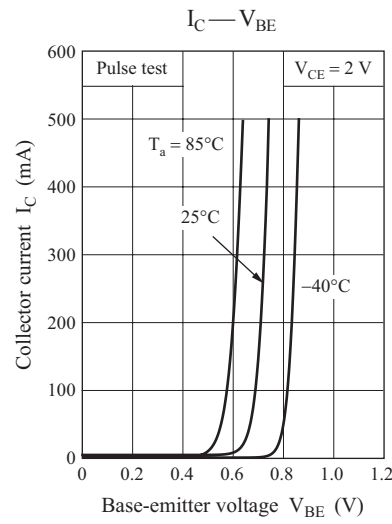
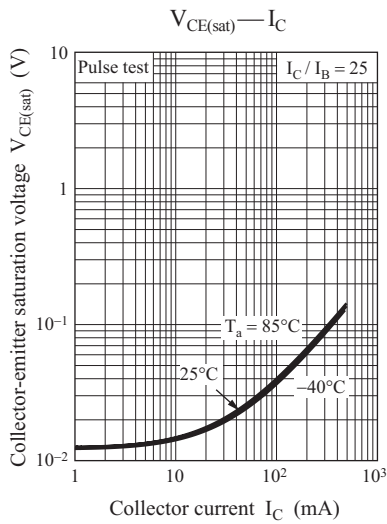
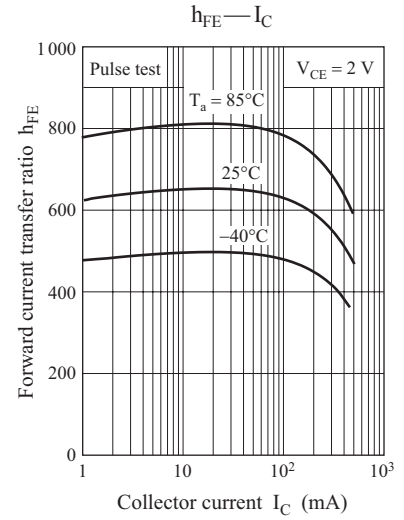
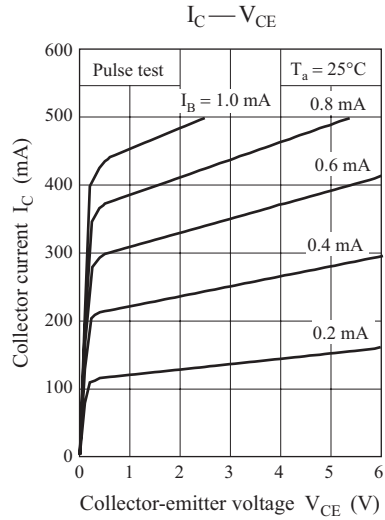
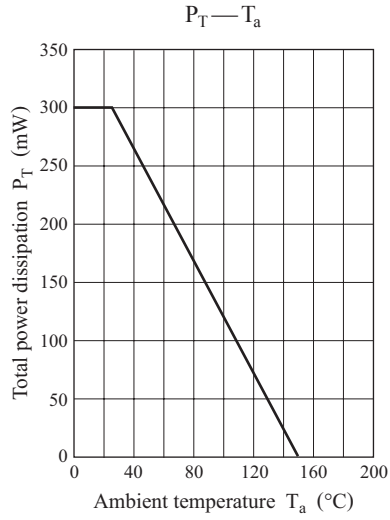
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	25			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	12			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_E = 0$			100	nA
Forward current transfer ratio *1	h_{FE}	$V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}$	200		800	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = 0.5 \text{ A}, I_B = 20 \text{ mA}$		0.18	0.40	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6		pF
ON resistance *2	R_{on}			1.0		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

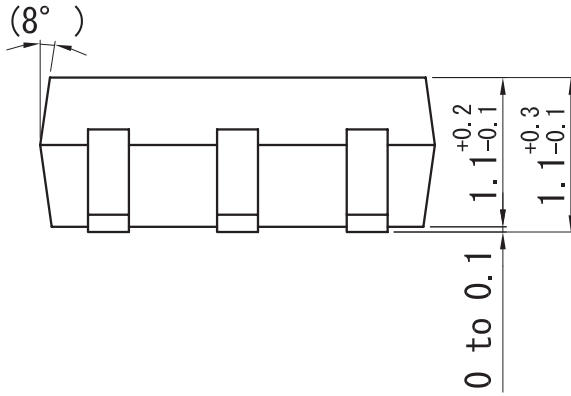
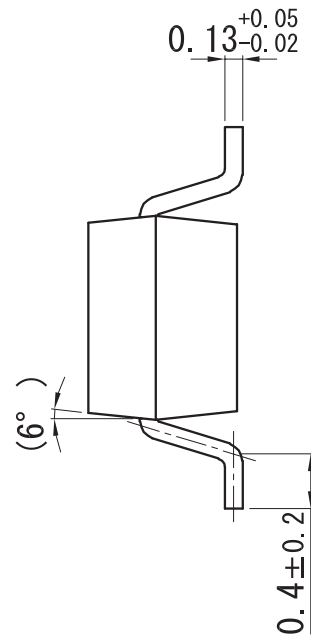
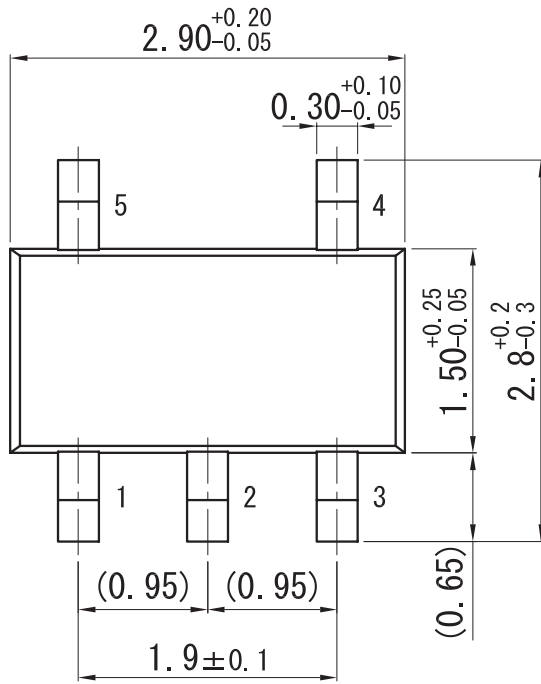
*2: R_{on} measurement circuit



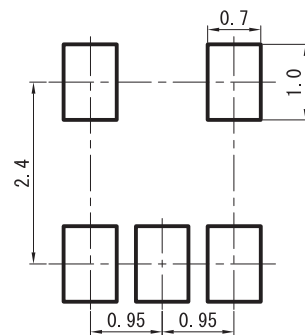


Mini5-G3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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